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2SC2714 NPN Transistors

SOT-23 Plastic-Encapsulate Transistors

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客户确认：

公司签章：

部门

工程部

品保部

采购部

签名

日期

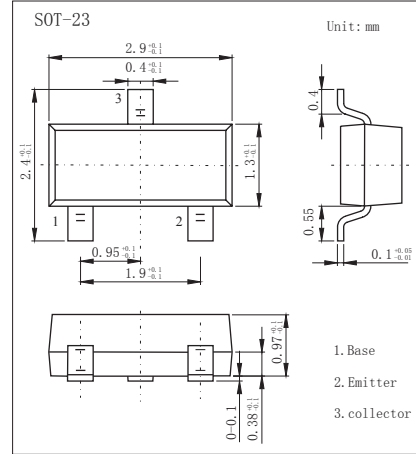


SOT-23 Plastic-Encapsulate Transistors

2SC2714 NPN Transistors

■ Features

- Collector Current Capability $I_c=20\text{mA}$
- Collector Emitter Voltage $V_{CE0}=30\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	30	
Emitter - Base Voltage	V_{EBO}	4	
Collector Current - Continuous	I_c	20	mA
Collector Power Dissipation	P_c	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1000	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c= 100 \mu\text{A}, I_E= 0$	40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c= 1 \text{ mA}, I_B= 0$	30			
Emitter - base breakdown voltage	V_{EBO}	$I_E= 100 \mu\text{A}, I_c= 0$	4			
Collector-base cut-off current	I_{CBO}	$V_{CB}= 18 \text{ V}, I_E= 0$			0.5	uA
Emitter cut-off current	I_{EBO}	$V_{EB}= 4 \text{ V}, I_c=0$			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=100 \text{ mA}, I_B=10\text{mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c=100 \text{ mA}, I_B=10\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE}= 6\text{V}, I_c= 1\text{mA}$	40		200	
Noise Figure	NF	$V_{CE}= 6\text{V}, I_E= -1\text{mA}, f=100\text{MHz}$		2.5	5	dB
Reverse Transfer capacitance	C_{re}	$V_{CB}= 6\text{V}, I_E= 0, f=1\text{MHz}$		0.7		pF
Transition frequency	f_T	$V_{CE}= 6\text{V}, I_c= 1\text{mA}$		550		MHz

■ Classification of h_{FE}

Type	2SC2714-R	2SC2714-O	2SC2714-Y
Range	40-80	70-140	100-200
Marking	QR	QO	QY

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■ Typical Characteristics

